WEST Search History

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DATE: Friday, March 18, 2005

Hide?	Set Name	Query	Hit Count
		DB=USPT; PLUR=YES; OP=ADJ	
☐	L16	l6 and cell adj2 characteristics	4
		DB=EPAB,JPAB; PLUR=YES; OP=ADJ	
☐	L15	L13 and write trip adj2 (voltage or potential or level)	0
☐	L14	L13 and write trip adj2 (voltage or potential or level or threshold)	0
☐	L13	SNM or static noise margin or noise margin	597
		DB=PGPB,USPT; PLUR=YES; OP=ADJ	
☐	L12	L6 and write adj2 (voltage or potential or level or threshold)	18
☐	L11	L6 and Vtrip	0
☐	L10	L6 and write trip	1
☐	L9	L6 and write trip adj2 (voltage or potential or level or threshold)	1
☐	L8	L6 and write trip adj2 (voltage or potential or level)	1
☐	L7	L6 and wire trip adj2 (voltage or potential or level)	0
☐	L6	L5 and (SNM or static noise margin or noise margin)	63
☐	L5	L4 and substrate	1289
☐	L4	L3 and well	1857
☐	L3	l2 and memory	2137
☐	L2	L1 and bias adj2 (voltage or supply or potential)	2197
☐	L1	SRAM or (static random access memory)	42189

END OF SEARCH HISTORY

VIET Q. NGUYEN
PRIMARY EXAMINER